

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	21	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or (NROM)) and ((ono or (oxide adj nitride adj oxide) or ((silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide))) and (dop\$6 or implant\$6)) and (bit adj line) and (word adj line)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 15:11
L2	148	"438"/\$.ccls. and ("ONO") and (etch adj stop) and (etch\$5 adj rat\$4) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 15:12
L3	165	"257"/\$.ccls. and ("ONO") and (etch adj stop) and (etch\$5 adj rat\$4) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 15:12
L4	570	semiconductor and ono and (etch adj stop) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 15:12
S1	12	((("6429063") or ("6417044") or ("6399441") or ("6395590") or ("6372564") or ("6346466") or ("6255166") or ("6583007") or ("6566203") or ("6555427") or ("6518125") or ("6482708"))).PN.	USPAT; USOCR	OR	OFF	2003/10/15 14:43
S2	2	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and (ono same (wet adj etching) same (dop\$6 or implant\$6) same (buried adj bit adj line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:33
S3	2	(ono same (wet adj etching) same (dop\$6 or implant\$6) same (buried adj bit adj line)) and ((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:12
S4	3	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (wet adj etching) and (dop\$6 or implant\$6) and (buried adj bit adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:15

S5	8	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (wet adj etching) and (dop\$6 or implant\$6) and (bit adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:27
S6	94	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (dop\$6 or implant\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:33
S7	94	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (dop\$6 or implant\$6)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:34
S8	81	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (dop\$6 or implant\$6)) and @ad<="20021115" and bit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:29
S9	72	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory)) and ono and (dop\$6 or implant\$6)) and @ad<="20021115" and (bit adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:34
S10	2	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or nrom) and (ono same (wet adj etching) same (dop\$6 or implant\$6) same (buried adj bit adj line))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:33
S11	157	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop\$6 or implant\$6)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:33
S12	150	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop\$6 or implant\$6)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:34
S13	115	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop\$6 or implant\$6)) and @ad<="20021115" and (bit adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:46

S14	85	(((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop\$6 or implant\$6)) and @ad<="20021115") and (bit adj line)) and (etch\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:49
S15	24	(((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop\$6 or implant\$6)) and @ad<="20021115") and (bit adj line)) and (wet adj etch\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:48
S16	30	(((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop\$6 or implant\$6)) and @ad<="20021115") and (bur\$4 adj bit adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:47
S17	6	(((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop\$6 or implant\$6)) and @ad<="20021115") and (bit adj line)) and (wet adj etch\$5)) and (bur\$4 adj bit adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:47
S18	6	(((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop\$6 or implant\$6)) and @ad<="20021115") and (bur\$4 adj bit adj line)) and (wet adj etch\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/02 14:49
S19	26	(((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or NROM) and ono and (dop\$6 or implant\$6)) and @ad<="20021115") and (bur\$4 adj bit adj line)) and (etch\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 07:57

S20	99	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or (NROM)) and ((ono or (oxide adj nitride adj oxide) or ((silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide))) and (dop\$6 or implant\$6) and @ad<="20021115") and (bit adj line) and (word adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 08:07
S21	1	("6566203").PN.	USPAT; USOCR	OR	OFF	2003/10/09 15:34
S22	1	("6461906").PN.	USPAT; USOCR	OR	OFF	2003/09/03 13:17
S23	1	("5496753").PN.	USPAT; USOCR	OR	OFF	2003/09/03 13:07
S24	329	(438/261).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/30 08:19
S25	1390	(438/257).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:09
S26	578	(438/258).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:08
S27	330	(438/259).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:08
S28	98	(438/260).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:08
S29	329	(438/261).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:08

S30	199	(438/262).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:08
S31	711	(438/526).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:09
S32	694	(438/275).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:09
S33	246	(438/294).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:10
S34	152	(438/216).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:10
S35	333	(438/591).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:10
S36	152	(438/216).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:10
S37	613	(438/264).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:11

S38	636	(438/527).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:12
S39	750	(438/287).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:12
S40	74	(438/954).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/09/03 13:12
S41	20	semiconductor same ono same (etch\$4 adj stop)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 15:28
S42	20	(semiconductor same ono same (etch\$4 adj stop)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/19 11:04
S43	480	semiconductor and ono and (etch adj stop) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 15:12
S44	12	438/287,261,591.ccls. and ono and (etch adj stop) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 08:19
S45	264	438/287,261,591.ccls. and ono and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 15:38
S46	397	"257"/\$.ccls. and ono and (etch\$3 adj stop\$4 adj (layer or film)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/15 14:52

S47	340	"438"/\$.ccls. and ono and (etch\$3 adj stop\$4 adj (layer or film)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/15 14:52
S48	502	ono and (etch\$3 adj stop\$4 adj (layer or film)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 08:20
S49	9	(ono same semiconductor same (etch\$3 adj stop\$4 adj (layer or film))) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/15 14:53
S50	478	ono and semiconductor and (etch\$3 adj stop\$4 adj (layer or film)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/15 15:34
S51	32968	liu.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/15 15:36
S52	10	liu.in. and cheng-jye	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/15 15:35
S53	2054	hsiung.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/15 15:36
S54	66294	chen.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/15 15:36
S55	3	hsiung.in. and tai-liang	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/15 15:37
S56	32	chen.in. and chia-hsing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/15 15:37

S57	1	("6376341").PN.	USPAT; USOCR	OR	OFF	2003/10/10 11:29
S58	3	((("6566203") or ("6461906") or ("5496753"))).PN.	USPAT; USOCR	OR	OFF	2003/10/10 10:48
S59	13	((("6429063") or ("6417044") or ("6399441") or ("6395590") or ("6372564") or ("6346466") or ("6255166") or ("6583007") or ("6566203") or ("6555427") or ("6518125") or ("6482708") or ("6376341"))).PN.	USPAT; USOCR	OR	OFF	2003/10/15 14:49
S60	14	((("6429063") or ("6417044") or ("6399441") or ("6395590") or ("6372564") or ("6346466") or ("6255166") or ("6583007") or ("6566203") or ("6555427") or ("6518125") or ("6482708") or ("6376341") or ("6538270"))).PN.	USPAT; USOCR	OR	OFF	2003/10/16 09:22
S61	2	((("6433384") or ("6472701"))).PN.	USPAT; USOCR	OR	OFF	2004/07/19 13:20
S62	65	("ONO") same (masking or protect\$5) same ((silicon adj nitride) or ("SiN")) same (pattern\$6 or (wet adj etch\$6))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/16 09:47
S63	63	("ONO") same (masking or protect\$5) same ((silicon adj nitride) or ("SiN")) same (pattern\$6 or (wet adj etch\$6)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/19 11:07
S64	128	(semiconductor same ono same ((etch\$4 adj stop) or (protect\$6))) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/19 11:05
S65	21	(semiconductor same ono same (etch\$4 adj stop)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/19 11:05
S66	13	438/287,261,591.ccls. and ono and (etch adj stop) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/19 11:06
S67	75	("ONO") same (masking or protect\$5) same ((silicon adj nitride) or ("SiN")) same (pattern\$6 or (wet adj etch\$6)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/19 11:07

S68	83	(((oxide adj nitride adj oxide) or ("ONO")) same (masking or protect\$5) same ((silicon adj nitride) or ("SiN")) same (pattern\$6 or (wet adj etch\$6))) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/07/19 12:50
S71	1	("5811315").PN.	USPAT; USOCR	OR	OFF	2004/07/19 13:20

S72	97	("3895360" "4016588" "4017888" "4145703" "4151021" "4173766" "4173791" "4257832" "4306353" "4342149" "4360900" "4380057" "4448400" "4471373" "4521796" "4527257" "4630085" "4667217" "4742491" "4769340" "4780424" "4847808" "4870470" "4941028" "5021999" "5075245" "5086325" "5094968" "5104819" "5159570" "5168334" "5172338" "5175120" "5214303" "5260593" "5305262" "5311049" "5324675" "5338954" "5349221" "5350710" "5359554" "5393701" "5394355" "5414693" "5418176" "5418743" "5422844" "5424567" "5426605" "5434825" "5436481" "5455793" "5467308" "5477499" "5496753" "5518942" "5523251" "5553018" "5592417" "5599727" "5606523" "5654568" "5656513" "5712814" "5726946" "5751037" "5754475" "5760445" "5768192" "5787036" "5793079" "5801076" "5812449" "5825686" "5836772" "5841700" "5847441" "5864164" "5870335" "5903031" "5946558" "5963412" "5973373" "5991202" "6011725" "6018186" "6020241" "6028324" "6030871" "6034403" "6034896" "6063666" "6081456" "6137718" "6201282" "6348711").PN.	USPAT	OR	ON	2003/09/02 14:04
S73	1	("20020187596").PN.	US-PGPUB; USOCR	OR	OFF	2003/09/02 14:19

S74	16	((("6534380") or ("5244819") or ("6548382") or ("6569749") or ("6451652") or ("6429062") or ("6399469") or ("6929290") or ("6297086") or ("6245629") or ("6218255") or ("6087225") or ("6033959") or ("5940698") or ("5920777") or ("5413948") or ("5324673"))).PN.	USPAT; USOCR	OR	OFF	2003/09/03 07:44
S75	15	((("6534380") or ("5244819") or ("6548382") or ("6451652") or ("6429062") or ("6399469") or ("6929290") or ("6297086") or ("6245629") or ("6218255") or ("6087225") or ("6033959") or ("5940698") or ("5920777") or ("5413948") or ("5324673"))).PN.	USPAT; USOCR	OR	OFF	2003/09/03 07:45
S76	378	((dual or double) adj gate adj field adj effect adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 08:45
S77	350	((dual or double) adj gate adj field adj effect adj transistor) and @ad<="20020313"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 08:47
S78	94	((dual or double) adj gate adj field adj effect adj transistor) and @ad<="20020313" and "257"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 08:48
S79	78	((dual or double) adj gate adj field adj effect adj transistor) and @ad<="20020313" and "257" and channel and source and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 08:49
S80	9	((("6316296") or ("6339002") or ("6365913") or ("6413802") or ("6483156") or ("6504173") or ("6611023") or ("5757038") or ("5773331"))).PN.	USPAT; USOCR	OR	OFF	2005/05/27 09:44
S81	0	((dual or two or double) adj gates) same (different adj (width or wide) adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:54
S82	0	((dual or two or double) adj gates) and (different adj (width or wide) adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:53

S83	0	((dual or double) adj gates) and (differen\$3 adj (width or wide) adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:55
S84	0	((dual or double) adj gates adj field adj effect adj transistor) same (differen\$3 adj (width or wide) adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:56
S85	0	((dual or double) adj gates adj field adj effect adj transistor) and (differen\$3 adj (width or wide) adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:56
S86	0	((dual or double) adj gates adj field adj effect adj transistor) and (differen\$3 adj width adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:56
S87	0	((dual or double) adj gates adj field adj effect adj transistor) and (differen\$3 adj (width or size) adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:57
S88	164	((dual or double) adj gates adj field adj effect adj transistor) and @ad<="20020313" and channel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:58
S89	69	((dual or double) adj gates adj field adj effect adj transistor) and @ad<="20020313" and channel) and width	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:58
S90	2	((dual or double) adj gates adj field adj effect adj transistor) and @ad<="20020313" and channel) and (different adj width)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:59
S91	47	((dual or double) adj gates adj field adj effect adj transistor) and @ad<="20020313" and channel) and width) and (different)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:59
S92	91	((dual or double) adj gates adj field adj effect adj transistor) and @ad<="20020313" and channel) and (width or wide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:59

S93	2	((dual or double) adj gates adj field adj effect adj transistor) and @ad<="20020313" and channel) and (different adj (width or wide or size))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:59
S94	106	((dual or double) adj gates adj field adj effect adj transistor) and @ad<="20020313" and channel) and (width or wide or size)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/09/03 10:59
S118	1	("20030109090").PN.	US-PGPUB; USOCR	OR	OFF	2003/09/03 13:17
S119	1	("20030119247").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/09/15 14:45
S120	1	("20030127693").PN.	US-PGPUB; USOCR	OR	OFF	2003/09/16 09:13
S121	1	("6242784").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2003/09/16 09:13
S122	1	("6555446").PN.	USPAT; USOCR	OR	OFF	2003/09/16 10:00
S124	1	("6555446").PN.	USPAT; USOCR	OR	OFF	2003/09/16 10:06
S125	2	("5409848" "5933729").PN.	USPAT	OR	ON	2003/10/09 15:26
S126	0	(gate adj (oxide or insulat\$5 or dielectric)) and (differen\$3 adj thickness) and ((plasma adj nitrid\$6) same oxidiz\$6 same hydrogen) and @ad<="20030408"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/10 10:04
S127	3	(gate adj (oxide or insulat\$5 or dielectric)) and (differen\$3 adj thickness) and (plasma adj nitrid\$6) and (oxidiz\$6 same hydrogen) and @ad<="20030408"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/10/10 10:03
S128	1	("6555446").PN.	USPAT; USOCR	OR	OFF	2003/10/10 11:02
S130	1	("6570256").PN.	USPAT; USOCR	OR	OFF	2003/10/10 11:15
S132	1	("6531325").PN.	USPAT; USOCR	OR	OFF	2003/10/10 11:19
S134	1	("6531325").PN.	USPAT; USOCR	OR	OFF	2003/10/10 11:28
S135	1	("6570256").PN.	USPAT; USOCR	OR	OFF	2003/10/10 11:28
S136	1	("6569751").PN.	USPAT; USOCR	OR	OFF	2003/10/10 11:30

S13 8	1	("5604357").PN.	USPAT; USOCR	OR	OFF	2003/10/16 08:53
S13 9	1	("20010032997").PN.	US-PGPUB; USOCR	OR	OFF	2003/10/16 08:41
S14 0	14	438/287,261,591.ccls. and ono and (etch adj stop) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 10:06
S14 1	2	((("6376341") or ("6538270")).PN.	USPAT; USOCR	OR	OFF	2005/05/27 09:44
S14 2	2	438/287,261,591.ccls. and ("ONO") and (etch adj stop) and (etch\$5 adj rat\$4) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 15:12
S14 3	148	"438"/\$.ccls. and ("ONO") and (etch adj stop) and (etch\$5 adj rat\$4) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 10:07
S14 4	162	"257"/\$.ccls. and ("ONO") and (etch adj stop) and (etch\$5 adj rat\$4) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 10:08
S14 5	91	"257"/\$.ccls. and ("ONO") and (protective adj (layer or film)) and (etch\$5 adj rat\$4) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 10:08
S14 6	70	"438"/\$.ccls. and ("ONO") and (protective adj (layer or film)) and (etch\$5 adj rat\$4) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/27 10:09
S14 7	62	"438"/\$.ccls. and ("ONO") and (protective adj (layer or film)) and (etch\$5 adj rat\$4) and @ad<="20021115"	USPAT	OR	ON	2005/05/27 10:10
S14 8	78	"257"/\$.ccls. and ("ONO") and (protective adj (layer or film)) and (etch\$5 adj rat\$4) and @ad<="20021115"	USPAT	OR	ON	2005/05/27 10:09
S14 9	0	"438"/\$.ccls. and ("ONO") with (protective adj (layer or film)) with (etch\$5 adj rat\$4) and @ad<="20021115"	USPAT	OR	ON	2005/05/27 10:10

S15 0	0	"257"/\$.ccls. and (("ONO") with (protective adj (layer or film)) with (etch\$5 adj rat\$4)) and @ad<="20021115"	USPAT	OR	ON	2005/05/27 10:10
S15 1	0	semiconductor and (("ONO") with (protective adj (layer or film)) with (etch\$5 adj rat\$4)) and @ad<="20021115"	USPAT	OR	ON	2005/05/27 10:11
S15 2	0	semiconductor and @ad<="20021115" and (("ONO") with (protective adj (layer or film)) with (etch\$5 adj rat\$4))	USPAT	OR	ON	2005/05/27 10:11
S15 3	3	semiconductor and @ad<="20021115" and (("ONO") same (protective adj (layer or film)) same (etch\$5 adj rat\$4))	USPAT	OR	ON	2005/05/27 10:17
S15 4	0	semiconductor and @ad<="20021115" and (("ONO") near (protective adj (layer or film)) near (etch\$5 adj rat\$4))	USPAT	OR	ON	2005/05/27 10:11
S15 5	3	semiconductor and @ad<="20021115" and (((oxide adj nitride adj oxide) or (oxide-nitride-oxide) or ("ONO")) same (protective adj (layer or film)) same (etch\$5 adj rat\$4))	USPAT	OR	ON	2005/05/27 10:19
S15 6	2	"438"/\$.ccls. and @ad<="20021115" and (((oxide adj nitride adj oxide) or (oxide-nitride-oxide) or ("ONO")) same (protective adj (layer or film)) same (etch\$5 adj rat\$4))	USPAT	OR	ON	2005/05/27 10:18
S15 7	4	"438"/\$.ccls. and @ad<="20021115" and (((oxide adj nitride adj oxide) or (oxide-nitride-oxide) or ("ONO")) same (protective adj (layer or film)) same (etch\$5 adj rat\$4))	US-PGPUB; USPAT	OR	ON	2005/05/27 10:18
S15 8	4	"257"/\$.ccls. and @ad<="20021115" and (((oxide adj nitride adj oxide) or (oxide-nitride-oxide) or ("ONO")) same (protective adj (layer or film)) same (etch\$5 adj rat\$4))	US-PGPUB; USPAT	OR	ON	2005/05/27 10:19

S15 9	21	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or (NROM)) and ((ono or (oxide adj nitride adj oxide) or ((silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide))) and (dop\$6 or implant\$6)) and (bit adj line) and (word adj line)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/28 15:11
S16 0	13	((nitride adj read adj only adj memory) or (nitride adj (read-only) adj memory) or (NROM)) and ((ono or (oxide adj nitride adj oxide) or ((silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide))) and (dop\$6 or implant\$6)) and (bit adj line) and (word adj line)).clm.	US-PGPUB	OR	ON	2005/09/30 08:08
S16 1	519	(438/261).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/30 08:19
S16 2	14	438/287,261,591.ccls. and ono and (etch adj stop) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 08:20
S16 3	590	ono and (etch\$3 adj stop\$4 adj (layer or film)) and @ad<="20021115"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 08:22
S16 4	2	("20040097045").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/30 08:22